



SHEET 1 OF 13

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Substitute for form 1449/PTO)				ATTY. DOCKET NO. 061282-0234		SERIAL NO. 10/574,863	
				APPLICANT Yuichiro SASAKI, et al.			
				FILING DATE April 06, 2006		GROUP 2823	
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		US 5,561,072	10-01-1996	SAITO			
		US 6,465,727 B2	10-15-2002	MARUYAMA et al.			
		US 6,653,699	11-2003	YANG, JEONG-HWAN			
		US 2005/0227463	10-2005	ITO et al.			
		US 6,713,819 B1	03/30/2004	En et al.			
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No	
		JP 9-199719	07-31-1997	TOSHIBA CORP			
		JP 5-206045	08-13-1993	HITACHI LTD			
		JP 58-97863	06-10-1983	TOSHIBA CORP			
		WO 98/34268	08-06-1998	ULTRATECH STEPPER INC			
		JP 6-310533	11-04-1994	FUJITSU LTD			
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
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		International Search Report corresponding to application no. PCT/JP2004/001473 dated April 13, 2004					
		D. Lenoble et al., "Reliable and enhanced performances of sub-0.1 μm pMOSFETs doped by low biased Plasma Doping", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 110-111, 2000.					
		Y. Kiyota, "Surface Reaction Doping using Gas Source for Ultra Shallow Junctions", Japan Society of Applied Physics, 2000.					
		Y. Kiyota, et al., "Role of hydrogen during rapid vapor-phase doping analyzed by x-ray photoelectron spectroscopy and Fourier-transform infrared-attenuated total reflection", Journal of Vacuum Science and Technology A 16 (1), pp. 1-5, Jan/Feb 1998.					
		Y. Kiyota, "Surface Reaction Doping using Gas Source for Ultra Shallow Junction", Silicon Technology No. 39, pp. 9-11, June 2002.					
		Y. Sasaki et al., "Gas Phase Doping at Room Temperature", Extended Abstracts of International Workshop on Junction Technology, pp. 39-40, 2002.					
		Y. Sasaki et al., "B ₂ H ₆ Plasma Doping with "In-situ He Pre-amorphization", 2004 Symposium on VLSI Technology Digest of Technical Papers, pp. 180-181.					
		Chinese Office Action issued in corresponding Chinese Patent Application No. CN 2004800046349, mailed March 30, 2007.					
EXAMINER				DATE CONSIDERED			

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WDC99 1538509-1.061282.0234

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		US 2006/0205192	09/2006	Walther et al.	
		US 5,969,398	10/1999	Murakami	
		US 6,051,482	04/2000	Yang	
		US 5,897,346	04/1999	Yamaguchi et al.	
		US			
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		JP 9-17867	01/17/1997	NKK Corp.			X

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		US Patent Application Serial No. 11/153,572	
		US Patent Application Serial No. 11/819,567	
		ITO, T., et al., "Improvement of Threshold Voltage Roll-off by Ultra-shallow Junction Formed by Flash Lamp Annealing", 2003, Symposium on VLSI Technology Digest of Technical Papers.	

EXAMINER

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		YAMASHITA, F., et al., "Direct Joule Heating of Nd-Fe-B Based Melt-Spun Powder and Zinc Binder", 1999, IEEE.					
		CHU, P.K., et al., "Part one of two, Plasma Doping: Progress and potential", SOLID STATE TECHNOLOGY, September 1999, pages 55-60, www.solid-state.com.					
		CHU, P.K., et al., "Part two of two, Plasma Doping: Progress and potential", SOLID STATE TECHNOLOGY, October 1999, pages 77-82, www.solid-state.com.					
		HORI, A., et al., "CMOS Device Technology toward 50 nm Region - Performance and Drain Architecture - ", IEDM, 1999, pages 641-644, IEEE.					
		KWOK, DIXON T.K., et al., "Energy distribution and depth profile in BF ₃ plasma doping", SURFACE AND COATINGS TECHNOLOGY, 2001, pages 146-150, vol. 136, Elsevier Science B.V.					
		YAMASHITA, F., et al., "Nd-Fe-B Thin Arc-shaped Bonded Magnets for Small DC Motors Prepared by Powder Compacting Press with Ion-Implanted Punches", J. MGN. SOC. JAPAN, 2001, pages 683-686, Vol. 25 No. 4-2.					
		YAMASHITA, F., et al., "Preparation of a Solid Rotor Composed of a Highly Dense Ring-Shaped RE Bonded Magnet and an Iron-Dust Core", TRANS. MAGN. SOC. JAPAN., 2002, pages 111-114, Vol. 2 No. 3.					
		MIZUNO, B., "Ultra Shallow Junction for sub-50NM CMOS - The role of Plasma Doping - ", UJTLab, pages 10-13, Ultimate Junction Technologies Inc.					
		SASAKI, Y., et al., "B ₂ H ₆ Plasma Doping with In-situ He Pre-amorphization", SYMPOSIUM ON VLSI TECHNOLOGY DIGEST OF TECHNICAL PAPERS, 2004, pages 180-181, IEEE.					
		SASAKI, Y., et al., "Plasma Doped Shallow Junction Formation", MATSUSHITA TECHNICAL JOURNAL, December 2004, pages 404-409, Vol. 50 No. 6.					
		TSUTSUI, K., et al., "Doping Effects from Neutral B ₂ H ₆ Gas Phase on Plasma Pretreated Si Substrates as a Possible Process in Plasma Doping", THE JAPAN SOCIETY OF APPLIED PHYSICS, 2005, pages 3903-0907, Vol. 44 No. 6A.					
		MIZUNO, B., et al., "De-Excitation Pathways of highly-Excited Self-Trapped Exciton and Electron Plus Self-Trapped Hole", JOURNAL OF THE PHYSICAL SOCIETY OF JAPAN, June 1983, pages 1901-1903, Vol. 52 No. 6.					
		MIZUNO, B., "Excitation-Induced Atomic Motion of Self-Trapped Excitons in RbCl: Reorientation and Defect Formation", JOURNAL OF THE PHYSICAL SOCIETY OF JAPAN, September 1986, pages 3258-3271, Vol. 55 No. 9.					
		MIZUNO, B., et al., "Effect of Hydrogen on Oxygen Removal from Silicon-Overlayer on Insulator formed by O ⁺ Implantation", pages 637-640, Semiconductor Research Center, Matsushita Electric Industrial Co., Ltd.					
		FUJITA, T., et al., "Electron Paramagnetic Resonance Studies of Defects in Oxygen-Implanted Silicon", JAPANESE JOURNAL OF APPLIED PHYSICS, July 1987, pages L1116-L1118, Vol. 26 No. 7.					
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		MIZUNO, B., et al., "Effective removal of oxygen from Si layer on burned oxide by implantation of hydrogen", J. APPL. PHYS., September 1987, pages 2566-2568, Vol. 62 No. 6.					
		MIZUNO, B., et al., "New doping method for subhalf micron trench sidewalls by using an electron cyclotron resonance plasma", APPL. PHYS. LETT., November 1988, pages 2059-2061, Vol. 53 no. 21, American Institute of Physics.					
		SHIMIZU, N., et al., "Reduction of Thickness Secondary Defects in MeV ion Implanted Silicon by Intrinsic Gettering", EXTENDED ABSTRACTS OF THE 21ST CONFERENCE ON SOLID STATE DEVICES AND MATERIALS, TOKYO, 1989, pages 177-180.					
		HORI, A., et al., "A 0.05 μ m-CMOS with Ultra Shallow Source/Drain Junctions Fabricated by 5KeV Ion Implantation and Rapid Thermal Annealing", 1994, pages 485-488, IEDM.					
		HORI, A., et al., "Fabrication and Characteristics of a Room Temperature 0.05 μ m-CMOS - Possibility and Design Concept of Sub-0.1 μ m MOS Devices -", TECHNICAL REPORT OF IEICE, 1995, pages 41-46, THE INSTITUTE OF ELECTRONICS, INFORMATION AND COMMUNICATION ENGINEERS.					
		MIZUNO, B., et al. "Plasma doping for silicon", SURFACE AND COATINGS TECHNOLOGY, 1996, pages 51-55, Vol. 85, Elsevier Science S.A.					
		MIZUNO, B., et al., "Plasma Doping of Boron for Fabricating the Surface Channel Sub-quarter micron PMOSFET", SYMPOSIUM ON VLSI TECHNOLOGY DIGEST OF TECHNICAL DIGEST OF TECHNICAL PAPERS, 1996, IEEE.					
		TAKASE, M., et al., "An evaluation method for a high concentration profile produced in very low energy doping processes", NUCLEAR INSTRUMENTS AND METHODS IN PHYSICS RESEARCH, 1997, pages 288-290, Vol. 121, Elsevier Science B.V.					
		TAKASE, M., et al., "Suppressing Ion Implantation Induced Oxide Charging by Utilizing Physically Damaged Oxide Region", JPN. J. APPL. PHYS., March 1997, pages 1618-1621, Vol. 36 Part 1, No. 3B.					
		MIZUNO, B., et al., "Plasma Doping", pages 165-170, Central Research Laboratory, Matsushita Electric Industrial Co., Ltd.					
		KADOKURA, M., et al., "Analysis and Design Of At-Cut Quartz Resonators by three dimensional finite element method", EEP-Vol. 19-1, ADVANCES IN ELECTRONIC PACKAGING, 1997, pages 1101-1108, Vol. 1, ASME 1997.					
		MIZUNO, B., et al., "Plasma Doping and Plasma-Less Doping of Semiconductor", MAT. RES. SOC. SYMP. PROC., 1997, pages 345-950, Vol. 438, MATERIALS RESEARCH SOCIETY.					
		TAKASE, M., et al, "New Doping Technology-Plasma Doping - for Next Generation CMOS process with Ultra Shallow Junction - LSI Yield and surface contamination issues -", 1997, pages B9-B12, IEEE					
		TAKASE, M., et al., "Shallow Source/Drain Extensions for pMOSFETs with High Activation and Low Process Damage Fabricated by Plasma Doping", IEDM, 1997, pages 475-478, IEEE					
		JIN, C.G., "Hard X-ray Photoelectron spectroscopy (HX-PES) study on chemical binding states of ultra shallow plasma-doped silicon layer for the application of advanced ULSI devices", 2006, pages 116-119, IEEE.					
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		MIZUNO, B., et al., "Plasma Doping and Subsequent Rapid Thermal Processing for Ultra Shallow Junction Formation", 13TH IEEE International Conference on Advanced Thermal Processing of Semiconductors - RTP, 2005, IEEE					
		MIZUNO, B., et al., "Plasma Doping", 2004, pages 423-427, IEEE.					
		SASAKI, Y., et al., "Gas Phase Doping at Room Temperature", Extended Abstract of International Workshop on Junction Technology, 2002, pages 39-40, Japan Society of Applied Physics.					
		SASAKI, Y., et al., "Helicon Wave Plasma Doping System", Extended Abstract of International Workshop on Junction Technology, 2002, pages 37-38, Japan Society of Applied Physics.					
		JIN, C.G., et al., "Estimation of Ultra-Shallow Plasma Doping (PD) Layer's Optical Absorption Properties by Spectroscopic Ellipsometry (SE)", 2004, Pages 102-103, IEEE.					
		SHIMIZU, N., et al., "Secondary Defect Reduction by Multiple MeV Boron Ion Implantation", Extended Abstract of the 22nd (1990 International) Conference on Solid State Devices and Materials, Sendai, 1990, pages 449-452.					
		SASAKI, Y., et al., "New method of Plasma doping with in-situ Helium pre-amorphization", Nuclear Instruments and Methods in Physics Research B 237, 2005, pages 41-45, ELSEVIER B.V.					
		JIN, C.G., "Ultra shallow p ⁺ /n junction formation by plasma doping (PD) and long pulse all solid-state laser annealing (ASLA) with selective absorption modulation", Nuclear Instruments and Methods in Physics Research B 237, 2005, pages 58-61, ELSEVIER B.V.					
		MIZUNO, B., et al., "Plasma Doping and Plasma-Less Doping for Si: Application to the sub-quarter micron Surface Channel PMOSFET and Solid Plasma Source Application for Safety Operation", Semiconductor Research Center, Matsushita Electric Industrial Co., Ltd.					
		LIU, H., et al., "A New Plasma-Aided Solid-Source Implantation Method for Ultra-Shallow p ⁺ /n Junction Fabrication", Engineering Research Center for Plasma-Aided Manufacturing, University of Wisconsin-Madison.					
		MIZUNO, B., "Plasma Doping into the Side-Wall of a Sub-0.5 μ m Width Trench", Extended Abstracts of the 19th Conference on Solid State Devices and Materials, Tokyo, 1987, pages 319-322.					
		MIZUNO, B., "Plasma Doping Technology", Applied Physics, 2001, pages 1458-1462, Vol. 70.					
		TAKASE, M., et al., "Shallow Source/Drain Extensions for pMOSFETs with High Activation and Low Process Damage Fabricated by Plasma Doping", TECHNICAL REPORT OF IEICE, 1998, The Institute of Electronics, Information and Communication Engineers.					
		MIZUNO, et al., "Ultralow Energy Doping Plasma Doping", Special Issue - Currently Developed Ion Engineering Technology-1.					
		MIZUNO, B., et al., "Plasma Based Ion Implantation - Plasma Doping", High Temperature Science Journal, May 1996, pages 114-120, Vol. 3 No. 22.					
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		TATSUMI, T., et al., "Multilevel Interconnection Technology using Fluorinated Amorphous Carbon films", 3p-ZX-3, Silicon Systems Research Laboratories, NEC Corporation.					
		MIZUNO, B., et al., "Plasma doping for fabricating ultra shallow junction, 3p-ZX-4, Matsushita Electric Industrial Co., Ltd.					
		ODA, H., et al., "Demand for Junction Technology in CMOS Transistors", 27a-ZL-1, 49th Applied Physics Lecture Series - Lecture Manuscripts, Comprehensive Lectures within the Area, 2002, Tokai University.					
		MIZUNO, B., et al., "Junction Technologies: Status Quo and Perspectives", 27a-ZL-2, Comprehensive Lectures within the Area.					
		HATA, N., et al., "Characterization of Low-k Dielectrics by Z-ray Scattering- Anisotropy in Pore Diameter and its Suppression", 26p-M-19, 63rd Applied Physics Lecture Series - Lecture Manuscripts, 2002, Niigaka University.					
		SHIMANUKI, J., et al., "Behavior of pores in a thin low-k film during anneal - Ex-situ TEM observation method", 26p-M-20.					
		SASAKI, Y., et al., "In-situ Beam Current Monitor for Ion Implanter", 25a-G-1, pages 768.					
		HIGAKI, R., et al., "Plasma Doping and Plasma Assisted Gas Doping", 25a-G-2, 63rd Applied Physics Lecture Series - Lecture Manuscripts, 2002, Niigaka University.					
		KUROSAWA, J., et al., "Development of Ni-B-P-Pt type liquid metal ion source for formation of Ni-nano dopant array by single ion implantation", 25a-G-3, 63rd Applied Physics Lecture Series - Lecture Manuscripts, 2002, Niigaka University.					
		IMAMURA, K., et al., "Development of key-techniques for co-doping of acceptor and donor by single ion implantation", 25a-G-4, 63rd Applied Physics Lecture Series - Lecture Manuscripts, 2002, Niigaka University.					
		YAMASHITA, K., et al., "Development of Flash Lamp Annealer for 300mm Wafers", 29p-ZW-10, 50th Applied Physics Lecture Series - Lecture Manuscripts, 2003, Shinagawa University.					
		KUBO, Y., et al., "Development of advance single ion implantor", 29p-ZW-11, 50th Applied Physics Lecture Series - Lecture Manuscripts, 2003, Shinagawa University.					
		HIGAKI, R., et al., "Dose Control of gas Phase Doping at Room Temperature" 29p-ZW-12, 50th Applied Physics Lecture Series - Lecture Manuscripts, 2003, Shinagawa University.					
		AKAMA, S., et al., "The Surface Reaction mechanism of Gas Phase Doping at Room Temperature", 29p-ZW-13, 50th Applied Physics Lecture Series - Lecture Manuscripts, 2003, Shinagawa University.					
		SASAKI, Y., et al., "Behavior of H and contamination in the Plasma Doping (PD) process", 29p-ZW-14, 50th Applied Physics Lecture Series - Lecture Manuscripts, 2003, Shinagawa University.					
		KUROBE, K., et al., "Ultra-shallow n+/p Junction Formation by Heat-assisted Excimer Laser Annealing", 29p-ZW-15, 50th Applied Physics Lecture Series - Lecture Manuscripts, 2003, Shinagawa University.					
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		FUJINAMI, M., et al., "Research in Pores and Oxygen Compound Deficits in Si Due to the Positron Annihilation Coincidence Doppler Broadening Method, Positron Annihilation Coincidence Doppler Broadening Methods for Vacancy-Oxygen Complexes in Si", 1a-A-8, 64th Applied Physics Lecture Series – Lecture Manuscripts, 2003, Fukuoka University.					
		MIYAGOE, T., et al., "Behavior Research on Deficits in Noble Gas Ion Implanted Si Using a Positron Beam, Positron beam study of defects induced by noble gas implanted Si", 1a-A-9, 64th Applied Physics Lecture Series – Lecture Manuscripts, 2003, Fukuoka University.					
		HIGAKI, R., et al., "Effects on the Substrate Surface conditions with Gas Doping Having Used Plasma Preprocessing, Effects of substrate surface condition on gas-phase doping using plasma pretreatment", 1a-A-10, 64th Applied Physics Lecture Series – Lecture Manuscripts, 2003, Fukuoka University.					
		ITOH, H., et al., "Ultra-low energy ion implantation in Si II", 30p-ZQ-9, Preprints of the 67th Meeting of the Japan Society of Applied Physics, 2006, Ritsumeikan University.					
		MATSUDA, T., et al., "Spike RTA Induced Changes in Chemical Bondings and Their Depth Profile of Plasma-doped Boron", 30p-ZQ-10, Preprints of the 67th Meeting of the Japan Society of Applied Physics, 2006, Ritsumeikan University.					
		TANAKA, Y., et al., "8nm (5E18cm ⁻²) Ultra Shallow Junction Formation by Double-Pulsed Green Laser Annealing", 30p-ZQ-11, Preprints of the 67th Meeting of the Japan Society of Applied Physics, 2006, Ritsumeikan University.					
		HAYA, A., et al., "Surface Modification of Plastic Substrate by Atomic Hydrogen Anneal and Effect of AHA to Film Deposition", 29p-SM-1, Preprints of the 54th Meeting of the Japan Society of Applied Physics and Related Societies, 2007, Aoyama Gakuin University.					
		OHASHI, Y., et al., "Effects of Hydrogenation on Chemical Activity of Defects in Polycrystalline Silicon Thin films", 29p-SM-2, Preprints of the 54th Meeting of the Japan Society of Applied Physics and Related Societies, 2007, Aoyama Gakuin University.					
		WATANABE, M., et al., "Study of Activated Boron Depth Profiles and Ultra-Shallow P+ Layers Formed by Plasma Doping Method", 29p-SM-3, Preprints of the 54th Meeting of the Japan Society of Applied Physics and Related Societies, 2007, Aoyama Gakuin University.					
		ISHIBA, T., et al., "Lattice Strains in High Energy Ion Implanted Silicon Subjected to Thermal Annealings", 27a-SN-13.					
		SHIMIZU, N., et al., "Secondary Defect Reduction of Multiple MeV Ion Implantation (II)", 27a-SN-14.					
		NAKATA, J., "The Low-Temperature Crystallization and Amorphization Mechanism of Amorphous Si by High Energy Heavy-Ion Beam Irradiation", 27a-SN-15.					
		MATSUMOTO, M., "The Influence of Pre-oxidation Cleaning on Growth of Oxide Film (II)", 28a-D-1.					
		UCHIDA, H., et al., "Influence of Cleaning methods on Dielectric Breakdown in Thin SiO ₂ ", 28a-D-2.					
		TAKIYAMA, M., et al., "Electrical Characteristics of Al MOS Diode Contaminated with Cu-I", 28a-D-3.					
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		SHIMIZU, N., et al., "Secondary Defect Reduction of Multiple MeV Ion Implantation (III)", 31a-X-5.					
		KIMOTO, K., et al., "Rapid Thermal Annealing for High-energy Ion Implanted Si (V)" 31a-X-6.					
		KOYAMA, Y., et al., "Rapid Thermal Annealing for High-energy Ion Implanted Si (VI)" 31a-X-7.					
		SUZUKI, H., et al., "Preamorphization by si Double Ion Implantation", 9p-C-12.					
		TAKAMATSU, H., et al., "Evaluation of Anneal Effect by Photoacoustic Displacement Measurement", 9p-C-13.					
		SHIMIZU, N., et al., "Effects of Junction Leakage Current Reduction of Additional High Energy Si Ion Implantation", 9p-C-14.					
		KATSUMOTO, M., et al., "The Effect of NH4OH/H2O2 Cleaning on C-V Characteristics of MOS Capacitor", 11p-B-12.					
		SHINNO, H., "Ellipsometric Measurements of Silicon Surfaces During Oxidation in R.F. Plasma", 11p-B-13.					
		MAEKAWA, M., et al., "Effect of H2SO4 Boiling on Silicon Surface", 11p-B-14.					
		MIZUNO, B., et al., "Plasma-assisted Impurity Doping for ULSIs", 28p-ZP-10.					
		ITATANI, R., "Introductory Talk, Matrial Processing Induced by Electron Beam", 28p-ZQ-1.					
		TANIMURA, S., et al., "D-255 Total Management System for VLSI Manufacturing, 1994 Spring Conference of the Institute of Electronics, Information and Communications Engineers, Matsushita Electric Industrial Co., Ltd.					
		MAEKAWA, T., et al., "Annealing of Ar ⁺ Implanted Damage" 30p-ZK-2.					
		OKAHISA, M., et al., "Electrical Properties of High Energy Boron-Implanted Layers in Si", 30p-ZK-3.					
		SHIMIZU, N., et al., "Effects of n ⁺ Layer Formation on Junction Leakage Current Using High Energy Ion Implantation", 30p-ZK-4.					
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		KINOSHITA, K., et al., "Optical Property Change of Silicon in Low Energy Ion Implantation (II)", 28a-ZW-8.					
		MIZUNO, B., et al., "A Sputtering Effect During the Ion Implantation with Low Energy", 28a-ZW-9.					
		KAGAWA, K., et al., "Effect of Charging During Ion Implantation on Devices", 28a-ZW-10.					
		MURAKOSHI, A., et al., "Formation of Ultra Shallow Diffusion Layer by Ultra Low Energy Ion Implantation", 26p-ZN-10.					
		MIZUNO, B., et al., "Plasma Doping Method", 26p-ZN-11.					
		FUKUDA, K., et al., "Fabrication of Ultra Shallow Junction by Spin-on Glass SiO ₂ Film" 26p-ZN-12.					
		ISHII, M., "Quantitative Analysis of rare-Gas Ion Bombardment Damage of Si Surface using XPS", 26p-ZP-6.					
		TAKASE, M., et al., "Evaluation Method of High concentration Profile for Low Energy Ion Implantation", 26p-ZP-7.					
		NAKAMURA, T., et al., "Influence of simultaneously Implanted As ⁺ ions on diffusivity and activation efficiency of B atoms Implanted into silicon", 26p-ZP-8.					
		AKIYAMA, H., et al., "The life-time control technique for power devices using high-energy heavy ion radiation", 28a-P-6.					
		TAKASE, M., et al., "The Identification of the Region of Ion Implantation Induced Physical Damaged Layer", 28a-P-7.					
		TAMURA, F., et al., "Measurement of the minority carrier lifetime for the Si epitaxial layer", 28a-P-8.					
		MIZUNO, B., et al., "Room Temperature Vapor Phase Doping (RTVD)", 28p-P-4.					
		MIZUNO, B., et al., "Plasma Doping Applicable to sub-1/4 micron PMOS", 28p-P-5.					
		KUJIRAI, H., et al., "Ultra-shallow, low resistance junction formation by solid-phase diffusion of boron from BSG", 28p-P-6.					
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		TAKASE, M., et al., "Dosage Control by Plasma Emission in Plasma Doping Process", 7a-P-2.					
		MURAKAMI, E., et al., "Formation of Ultrashallow Junctions by Sb Selective δ Doping Technique", 7a-P-3.					
		KIYOTA, Y., et al., "the Role of Hydrogen during Rapid Vapor-phase Doping Analyzed by FTIR-ATR, 7a-P-4.					
		TAKASE, M., et al., "Fabrication of Low Sheet Resistance and Shallow Source/Drain Junction with Plasma Doping Process", 29a-G-2.					
		SHIMADA, N., et al., "Shallow Junction, Formation by Polyatomic Cluster Ion Implantation", 29a-G-3.					
		ISHIKAWA, T., et al., "Formation of shallow junctions by low-energy implantation", 29a-G-4.					
		SHIMADA, N., et al., "Shallow Junction Formation by Decaborane Ion Impantation (IV)", 3a-PC-13.					
		MINEJI, A., et al., "Shallow Junction Formation by 0.2 keV-single B Ion Implantation", 3a-PC-14.					
		TAKASE, M., et al., "High Activation Ultra Shallow Source/Drain Junction Fabricated by Plasma Doping", 3a-PC-15.					
		NISHIDA, S., et al., "the Herzog correction revisited", 7a-YP-8.					
		ONO, S., et al., "Design of a cryogenic current measuring device using a SQUID for low-intensity beams", 7a-YP-9.					
		HARUYAMA, Y., et al., "High resolution measurement of HeH ⁺ dissociative recombination with superconductor electron cooler", 7a-YP-10.					
		TSURUBUCHI, S., et al., "Excitation cross sections for the resonance states of the Ne by electron impact", 7a-YP-11.					
		WAKABAYASHI, et al., "IEDM Focusing on high speed and low electric power techniques, Finally the Cu damascene technique for practical applications has arrived", IEDM Conference, 1997, IEEE.					
		NAKATA, K., et al., "Fail Bit map Correlation Analysis System", The Institute of Electronics, Information and Communication Engineers (IEICE) Electronics Society Annual Meeting, 1995.					
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		TSUBO, Y., et al., "Diffusion of Phosphorus from P-doped Polysilicon through Ultrathin SiO ₂ into Si Substrate", 30p-ZP-11.					
		AOYAMA, T., et al., "Boron Diffusion in Silicon Dioxide in the Presence of Hydrogen and Fluorine", 30p-ZP-12.					
		TAKASE, M., et al., "Effect of oxide thickness on boron profile in the plasma doping process", 30p-ZP-13.					
		MIZUNO, B., et al., "Plasma Doping", Invitational Lecture.					
		TAKASE, M., et al., "Plasma doping Technology for the MOS transistor with a channel length below 0.15 μm", Applied Physics, 1999, Vol. 68 No. 5.					
		SASAKI, Y., et al., "Nondestructive Beam Current Monitor Using DC SQUID", pages 68-76.					
		KOBAYASHI, K., et al., "Three-Dimensional Plasma Doping for Beam-Channel Transistor", 29p-ZG-13, Preprints of the 51st Spring meeting of the Japan Society of Applied Physics and Related Societies, March 2004, Tokyo University of Technology.					
		SATO, T., et al., "Effect of wet cleaning treatment on dose of impurity after plasma doping", 29p-ZG-14, Preprints of the 51st Spring meeting of the Japan Society of Applied Physics and Related Societies, March 2004, Tokyo University of Technology.					
		TAKAGI, K., et al., "Profile control by Helium plasma treatment in plasma doping method", 29p-ZG-15, Preprints of the 51st Spring meeting of the Japan Society of Applied Physics and Related Societies, March 2004, Tokyo University of Technology.					
		OKASHITA, K., et al., "In-situ Plasma Pre-amorphization for Shallow Junction Formation", 3p-P10-14, Preprints of the 65th Meeting of the Japan Society of Applied Physics and Related Societies, September 2004, Tohoku Gakuin University.					
		NAKAZAWA, H., et al., "Characterization of Boron/Phosphorus Layer by Cold/Heat Ion Implantation", 3p-P10-15, Preprints of the 65th Meeting of the Japan Society of Applied Physics and Related Societies, September 2004, Tohoku Gakuin University.					
		KOBAYASHI, K., et al., "Doping Profile Evaluation for Three-Dimensional Transistor", 3p-P10-16, Preprints of the 65th Meeting of the Japan Society of Applied Physics and Related Societies, September 2004, Tohoku Gakuin University.					
		OTAKAGI, K., et al., "Effect on Impurity profile of Helium Plasma Treatment on a Plasma Doping Method", 65th Japan Society of Applied Physics Symposium Collection of Lectures, September 2004, Tohoku Graduate Department.					
		SAUDDIN, H., et al., "Leakage Current in Mesa-type p ⁺ /n, Junctions Formed by Plasma Doping", 10a-A-10, PerPreprints of the 66th Meeting of the Japan Society of Applied Physics, 2005, Tokushima University.					
		FUKAGAWA, Y., et al., "Electrical Properties of ultra-Shallow p ⁺ Layers Formed by Plasma Doping", 10a-A-11, PerPreprints of the 66th Meeting of the Japan Society of Applied Physics, 2005, Tokushima University.					
		MATSUDA, T., et al., "Chemical Bonds of Boron Atoms Implanted in A Silicon Surface by Plasma Doping", 10a-A-12, PerPreprints of the 66th Meeting of the Japan Society of Applied Physics, 2005, Tokushima University.					
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		MIZUNO, B., et al., "Reduction of lattice defect in Si layer on buried oxide by implantation of hydrogen," SDM 87-169, Basic Research Lab., Semiconductor Research Center, Matsushita Electric Industrial Co., Ltd.					
		MIZUNO, B., et al., "ECR Plasma Doping", SDM 88-95, Semiconductor Research Center, Semiconductor Basic Research Lab., Matsushita Electric Industrial Co., Ltd.					
		MIZUNO, B., et al., "ECR Plasma Doping", Electronic Material, December 1987.					
		MIZUNO, B., "Plasma Doping Technology", Semiconductor Research Center, Matsushita Electric Industrial Co., Ltd.					
		NAKADA, K., et al., "D-259 Development of Cleanroom Auto Control System", 1994 Spring Conference of the Society of Electronic Information and Communications.					
		MIZUNO, B., et al., "Behavior of Implanted Ions Near the Surface - Outer Diffusion and Self-sputtering", 28p-ZL1.					
		YAMANISHI, Y., et al., "Behavior during Oxidation of Nitrogen Introduced by Ion Implantation", 28p-ZL2.					
		ZAIZU, Y., et al., "Effects of Silicon Nitride Films on Boron Enhanced Diffusion and Crystalline Defects due to Boron Implantation", 28p-ZL3.					
		MIZUNO, B., et al., "Behavior near Surface of Implanted Ions (cont'd) Self-sputtering and Back-scattering", 20p-ZE-11.					
		KINOSHITA K., et al., "Optical Changes in Association with Crystalline Damage due to Low Energy Ion Implantation (IV)", 20p-ZE-12.					
		HASEGAWA, K., et al., "Dual Species (B, As) Implantation in Silicon", 28p-ZE-13.					
		SATO, T., et al., "Dose Volume changes and HF Cleansing Before and After Plasma Doping Change dose caused by HF treatment before and after plasma doping", 1a-A-11, 64th Applied Physics Lecture Series- Lecture Manuscripts, 2003, Fukuoka University.					
		SUSUKI, K., "High Tilt Angle Ion Implantation in Polycrystalline Si, High tilt angle ion implantation into Polycrystalline silicon", 1p-A-1, 64th Applied Physics Lecture Series- Lecture Manuscripts, 2003, Fukuoka University.					
		YAMADA, M., et al., "Evaluation of Junction Leak Current Caused by Element Isolation Stress, Study of junction leakage currents induced by the stress of shallow trench isolation", 1p-A-2, 64th Applied Physics Lecture Series- Lecture Manuscripts, 2003, Fukuoka University.					
		AIBA, I., et al., "Dose Variation by Chemical Cleaning Process after Plasma Doping", 3p-P10-18, 65th Japan Society of Applied Physics Symposium Collection of Lectures, September 2004, Tohoku Graduate Department.					
		MAJIMA, M., et al., "Hall Effect Measurement of ultra Shallow p ⁺ n Junctions formed by Plasma Doping", 3p-P10-19, 65th Japan Society of Applied Physics Symposium Collection of Lectures, September 2004, Tohoku Graduate Department.					
		MASUDA, T., et al., "Amorphization of Large-scale Silicon Substrate by using hybrid Quantum Chemical Molecular Dynamics Method", 1a-YE-7, 52nd Japan Society of Applied Physics Symposium Collection of Lectures, 2005, Saitama University.					
		FUKUGAWA, Y., et al., "Examination of pre-amorphous layer formation process by He plasma irradiation", 1a-YE-8, 52nd Japan Society of Applied Physics Symposium Collection of Lectures, 2005, Saitama University.					
		AIBA, I., et al., "Plasma Doping on Si substrates with Resist Patterns", 1a-YE-9, 52nd Japan Society of Applied Physics Symposium Collection of Lectures, 2005, Saitama University.					
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		OKASHITE, K., et al., "Ultra Shallow Junction Formation with Plasma Doping and Spike RTA", 1a-YE-10, 52nd Japan Society of Applied Physics Symposium Collection of Lectures, 2005, Saitama University.					
		SAUDDIN, H., "Leakage Current Characteristics of Ultra-shallow p+/n Junctions Formed by Plasma Doping", 1a-YE-11, 52nd Japan Society of Applied Physics Symposium Collection of Lectures, 2005, Saitama University.					
		MATSUNO, A., et al., "One Dimensional Thermal Diffusion Simulation for the USJ formation by green laser anneal with absorption layer", 16-YE-1, 52nd Japan Society of Applied Physics Symposium Collection of Lectures, 2005, Saitama University.					
		MIZUNO, B., et al., "ECR Plasma Doping", Matsushita Electric Industrial Co., Ltd.					
		HIGAKI, R., et al., "Effects of gas phase absorption into Si substrates on plasma doping process".					
		LENOBLE, D., et al., "Fabrication of 60-nm plasma doped CMOS transistors", 2002, IEEE.					
		SEVERI, S., et al., "Diffusion-less junctions and super halo profiles for PMOS transistors formed by SPER and FUSI gate in 45nm physical gate length devices", 2004, IEEE.					
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